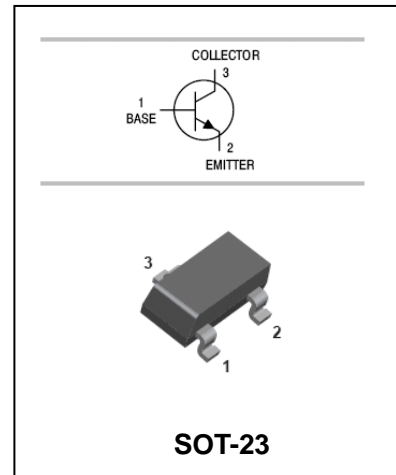


## NPN Silicon Epitaxial Planar Transistor

## KTD1304

### FEATURES

- High emitter-base voltage.
- High reverse  $h_{FE}$ .
- Low on resistance.



### APPLICATIONS

- Audio muting application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
KTD1304	MAX	SOT-23

### MAXIMUM RATING @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	25	V
$V_{CEO}$	Collector-Emitter Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	12	V
$I_C$	Collector Current -Continuous	300	mA
$I_B$	Base Current	30	mA
$P_C$	Collector Power Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55~150	$^{\circ}\text{C}$

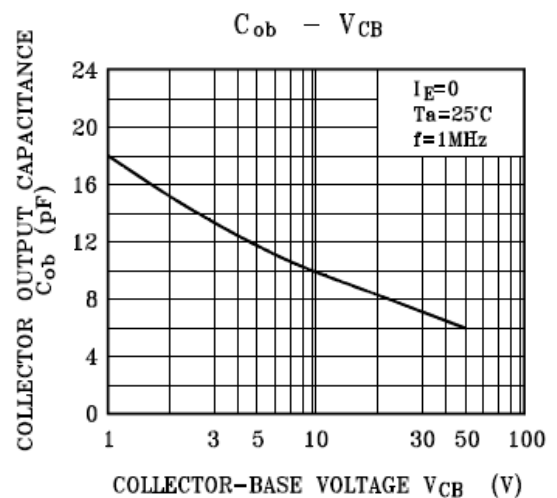
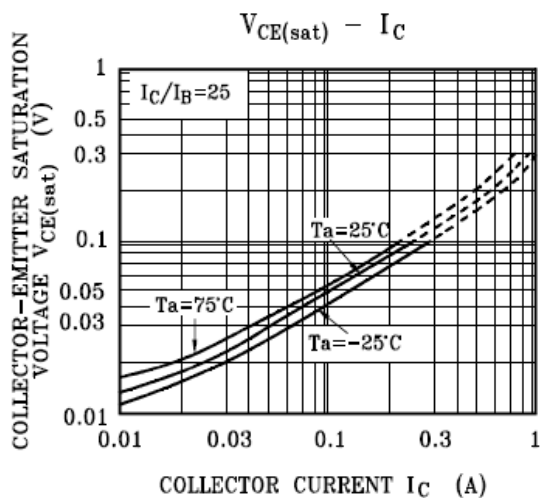
## NPN Silicon Epitaxial Planar Transistor

## KTD1304

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

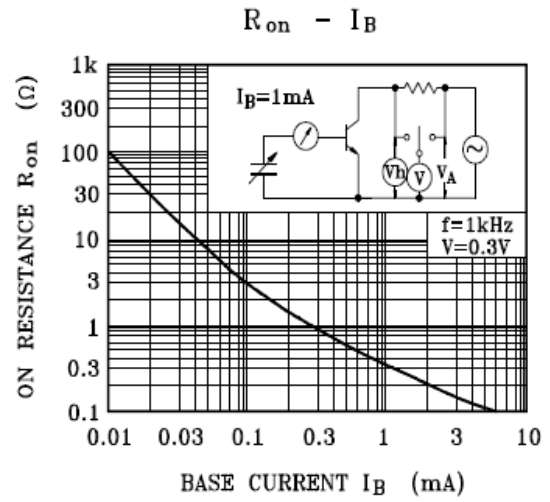
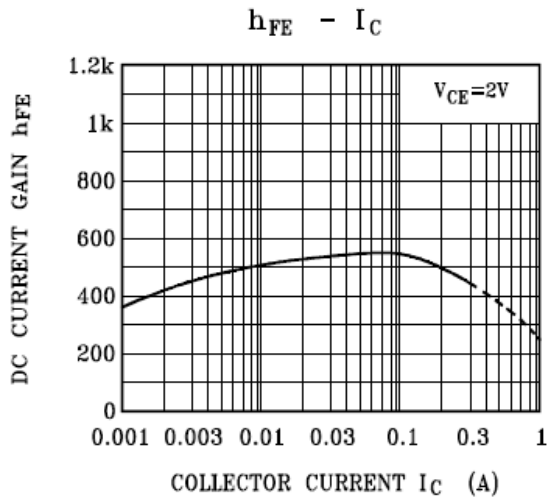
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	12			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=25V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=12V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=2V, I_C=4mA$	200		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=1mA$	60			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$			10	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



## NPN Silicon Epitaxial Planar Transistor

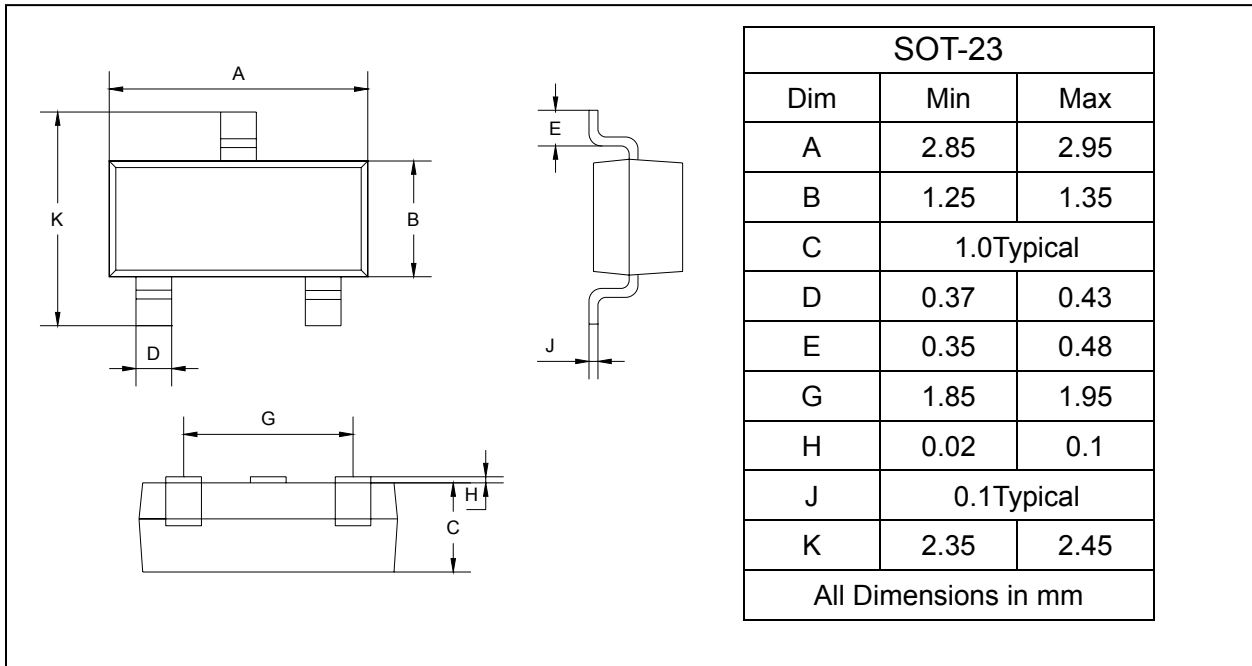
## KTD1304



### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



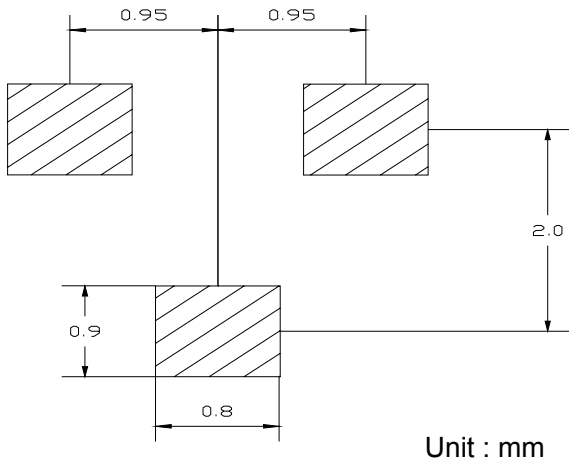
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## NPN Silicon Epitaxial Planar Transistor

## KTD1304

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### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
KTD1304	SOT-23	3000/Tape&Reel